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Section I. (Amendment to the Claims)

Please cancel claims 39-60, 62, 68-69, and 72-76, as in the following list of claims 1-76.

1-38. (Cancelled)

39-60. (Cancelled).

61. (Previously presented) A method of making a single crystal GaN substrate, comprising growing single crystal GaN over a substrate heterogeneous to GaN, and removing the heterogeneous substrate to yield the single crystal GaN substrate.

62. (Cancelled).

63. (Previously presented) A method of making a single crystal GaN substrate, including the steps of:

providing a substrate heterogeneous to GaN, having one or more intermediate layers thereon;

growing a layer of single crystal GaN over said one or more intermediate layers to form an article including the heterogeneous substrate, one or more intermediate layers, and said layer of single crystal GaN; and

removing the heterogeneous substrate from the article.

64. (Original) The method of claim 63, wherein the one or more intermediate layers includes a buffer layer.

65. (Original) The method of claim 63, wherein the one or more intermediate layers includes a template layer for subsequent GaN growth thereon.

66. (Original) The method of claim 63, wherein the one or more intermediate layers includes a protective layer.

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67. (Original) The method of claim 63, wherein the one or more intermediate layers includes an etch stop layer.
- 68-69. (Cancelled).
70. (Previously presented) A method of forming a GaN single crystal substrate, comprising:
- growing single crystal GaN on a gallium arsenide substrate; and
- etching the gallium arsenide substrate to remove same and yield the GaN single crystal substrate.
71. (Original) The method of claim 70, wherein the gallium arsenide substrate is etched away *in situ* at a temperature within 300°C of the growth temperature of the GaN on the gallium arsenide substrate.
- 72-76. (Cancelled).